



Welcome to [E-XFL.COM](#)

What is "[Embedded - Microcontrollers](#)"?

"[Embedded - Microcontrollers](#)" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "[Embedded - Microcontrollers](#)"

Details

Product Status	Active
Core Processor	ARM® Cortex®-M3
Core Size	32-Bit Single-Core
Speed	32MHz
Connectivity	I ² C, IrDA, LINbus, SPI, UART/USART, USB
Peripherals	Brown-out Detect/Reset, Cap Sense, DMA, I ² S, POR, PWM, WDT
Number of I/O	83
Program Memory Size	64KB (64K x 8)
Program Memory Type	FLASH
EEPROM Size	4K x 8
RAM Size	32K x 8
Voltage - Supply (Vcc/Vdd)	1.8V ~ 3.6V
Data Converters	A/D 24x12b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	100-LQFP
Supplier Device Package	100-LQFP (14x14)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32l151v8t6a

	package outline.	121
Figure 46.	TFBGA64, 5 x 5 mm, 0.5 mm pitch, thin fine-pitch ball grid array package recommended footprint	122
Figure 47.	TFBGA64 5 x 5 mm, 0.5 mm pitch, package top view example.	123
Figure 48.	Thermal resistance suffix 6.	125
Figure 49.	Thermal resistance suffix 7.	125

2.1 Device overview

Table 2. Ultra-low-power STM32L151x6/8/B-A and STM32L152x6/8/B-A device features and peripheral counts

Peripheral		STM32L15xCxxxA			STM32L15xRxxxA			STM32L15xVxxxA	
Flash (Kbytes)		32	64	128	32	64	128	64	128
Data EEPROM (Kbytes)		4							
RAM (Kbytes)		16	32	32	16	32	32	32	32
Timers	General-purpose	6							
	Basic	2							
Communication interfaces	SPI	2							
	I ² C	2							
	USART	3							
	USB	1							
GPIOs		37			51/50 ⁽¹⁾			83	
12-bit synchronized ADC Number of channels		1 14 channels			1 20/19 channels ⁽¹⁾			1 24 channels	
12-bit DAC Number of channels		2 2							
LCD (STM32L152xxxxA Only) COM x SEG		4x16			4x32/4x31 ⁽¹⁾ 8x28/8x27 ⁽¹⁾			4x44 8x40	
Comparator		2							
Capacitive sensing channels		13			20				
Max. CPU frequency		32 MHz							
Operating voltage		1.8 V to 3.6 V (down to 1.65 V at power-down) with BOR option 1.65 V to 3.6 V without BOR option							
Operating temperatures		Ambient operating temperatures: −40 to +85 °C / −40 to + 105 °C Junction temperature: -40 to +110°C							
Packages		LQFP48, UFQFPN48			LQFP64, TFBGA64			LQFP100, UFBGA100	

1. For TFBGA64 package (instead of PC3 pin there is V_{REF+} pin).

2.2 Ultra-low-power device continuum

The ultra-low-power family offers a large choice of cores and features. From a proprietary 8-bit core up to the Cortex-M3, including the Cortex-M0+, the STM8Lx and STM32Lx series offer the best range of choices to meet your requirements in terms of ultra-low-power features. The STM32 Ultra-low-power series is an ideal fit for applications like gas/water meters, keyboard/mouse, or wearable devices for fitness and healthcare. Numerous built-in features like LCD drivers, dual-bank memory, low-power Run mode, op-amp, AES-128bit, DAC, crystal-less USB and many others, allow to build highly cost-optimized applications by reducing the BOM.

Note: STMicroelectronics as a reliable and long-term manufacturer ensures as much as possible the pin-to-pin compatibility between any STM8Lx and STM32Lx devices and between any of the STM32Lx and STM32Fx series. Thanks to this unprecedented scalability, your existing applications can be upgraded to respond to the latest market features and efficiency demand.

2.2.1 Performance

All families incorporate highly energy-efficient cores with both Harvard architecture and pipelined execution: advanced STM8 core for STM8L families and ARM Cortex-M3 core for STM32L family. In addition specific care for the design architecture has been taken to optimize the mA/DMIPS and mA/MHz ratios.

This allows the ultra-Low-power performance to range from 5 up to 33.3 DMIPs.

2.2.2 Shared peripherals

STM8L15xxx and STM32L1xxxx share identical peripherals which ensure a very easy migration from one family to another:

- Analog peripherals: ADC, DAC and comparators
- Digital peripherals: RTC and some communication interfaces

2.2.3 Common system strategy

To offer flexibility and optimize performance, the STM8L15xxx and STM32L1xxxx families use a common architecture:

- Common power supply range from 1.65 V to 3.6 V, (1.65 V at power down only for STM8L15xxx devices)
- Architecture optimized to reach ultra-low consumption both in low-power modes and Run mode
- Fast startup strategy from low-power modes
- Flexible system clock
- Ultra-safe reset: same reset strategy including power-on reset, power-down reset, brownout reset and programmable voltage detector.

2.2.4 Features

ST ultra-low-power continuum also lies in feature compatibility:

- More than 10 packages with pin count from 20 to 144 pins and size down to 3 x 3 mm
- Memory density ranging from 4 to 512 Kbytes

Five BOR thresholds are available through option bytes, starting from 1.8 V to 3 V. To reduce the power consumption in Stop mode, it is possible to automatically switch off the internal reference voltage (V_{REFINT}) in Stop mode. The device remains in reset mode when V_{DD} is below a specified threshold, $V_{POR/PDR}$ or V_{BOR} , without the need for any external reset circuit.

Note: The start-up time at power-on is typically 3.3 ms when BOR is active at power-up, the start-up time at power-on can be decreased down to 1 ms typically for devices with BOR inactive at power-up.

The device features an embedded programmable voltage detector (PVD) that monitors the V_{DD}/V_{DDA} power supply and compares it to the V_{PVD} threshold. This PVD offers 7 different levels between 1.85 V and 3.05 V, chosen by software, with a step around 200 mV. An interrupt can be generated when V_{DD}/V_{DDA} drops below the V_{PVD} threshold and/or when V_{DD}/V_{DDA} is higher than the V_{PVD} threshold. The interrupt service routine can then generate a warning message and/or put the MCU into a safe state. The PVD is enabled by software.

3.3.3 Voltage regulator

The regulator has three operation modes: main (MR), low-power (LPR) and power down.

- MR is used in Run mode (nominal regulation)
- LPR is used in the Low-power run, Low-power sleep and Stop modes
- Power down is used in Standby mode. The regulator output is high impedance, the kernel circuitry is powered down, inducing zero consumption but the contents of the registers and RAM are lost except for the standby circuitry (wakeup logic, IWDG, RTC, LSI, LSE crystal 32K osc, RCC_CSR).

3.3.4 Boot modes

At startup, boot pins are used to select one of three boot options:

- Boot from Flash memory
- Boot from System Memory
- Boot from embedded RAM

The boot loader is located in System Memory. It is used to reprogram the Flash memory by using USART1 or USART2. See the application note “STM32 microcontroller system memory boot mode” (AN2606) for details.

3.12 Ultra-low-power comparators and reference voltage

The STM32L151x6/8/B-A and STM32L152x6/8/B-A devices embed two comparators sharing the same current bias and reference voltage. The reference voltage can be internal or external (coming from an I/O).

- one comparator with fixed threshold
- one comparator with rail-to-rail inputs, fast or slow mode. The threshold can be one of the following:
 - DAC output
 - External I/O
 - Internal reference voltage (V_{REFINT}) or V_{REFINT} submultiple (1/4, 1/2, 3/4)

Both comparators can wake up from Stop mode, and be combined into a window comparator.

The internal reference voltage is available externally via a low-power / low-current output buffer (driving current capability of 1 μ A typical).

3.13 Routing interface

The highly flexible routing interface allows the application firmware to control the routing of different I/Os to the TIM2, TIM3 and TIM4 timer input captures. It also controls the routing of internal analog signals to ADC1, COMP1 and COMP2 and the internal reference voltage V_{REFINT} .

3.14 Touch sensing

The STM32L151x6/8/B-A and STM32L152x6/8/B-A devices provide a simple solution for adding capacitive sensing functionality to any application. These devices offer up to 20 capacitive sensing channels distributed over 10 analog I/O groups. Both software and timer capacitive sensing acquisition modes are supported.

Capacitive sensing technology is able to detect the presence of a finger near a sensor which is protected from direct touch by a dielectric (glass, plastic, ...). The capacitive variation introduced by the finger (or any conductive object) is measured using a proven implementation based on a surface charge transfer acquisition principle. It consists of charging the sensor capacitance and then transferring a part of the accumulated charges into a sampling capacitor until the voltage across this capacitor has reached a specific threshold. The capacitive sensing acquisition only requires few external components to operate. This acquisition is managed directly by the GPIOs, timers and analog I/O groups (see [Section 3.13: Routing interface](#)).

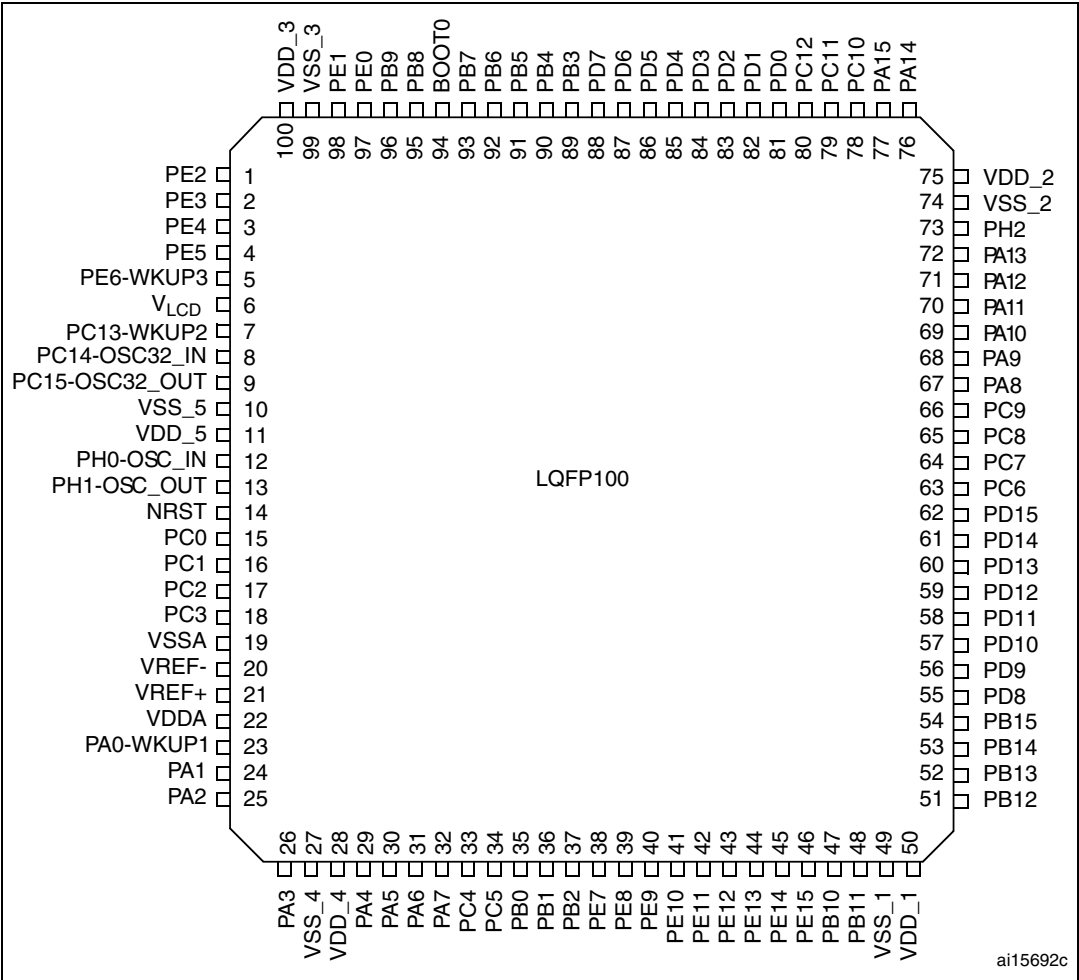
Reliable touch sensing functionality can be quickly and easily implemented using the free STM32L1xx STMTouch touch sensing firmware library.

3.15 Timers and watchdogs

The ultra-low-power STM32L151x6/8/B-A and STM32L152x6/8/B-A devices include six general-purpose timers, two basic timers and two watchdog timers.

[Table 7](#) compares the features of the general-purpose and basic timers.

Figure 4. STM32L15xVxxxA LQFP100 pinout



1. This figure shows the package top view.

Table 9. STM32L151x6/8/B-A and STM32L152x6/8/B-A pin definitions (continued)

Pins					Pin name	Pin type ⁽¹⁾	I/O structure	Main function ⁽²⁾ (after reset)	Pins functions	
LQFP100	LQFP64	TFBGA64	UFBGA100	LQFP48 or UQFPN48					Alternate functions	Additional functions
67	41	D7	D11	29	PA8	I/O	FT	PA8	USART1_CK/MCO/ LCD_COM0	-
68	42	C7	D10	30	PA9	I/O	FT	PA9	USART1_TX/ LCD_COM1	-
69	43	C6	C12	31	PA10	I/O	FT	PA10	USART1_RX/ LCD_COM2	-
70	44	C8	B12	32	PA11	I/O	FT	PA11	USART1_CTS/ SPI1_MISO	USB_DM
71	45	B8	A12	33	PA12	I/O	FT	PA12	USART1_RTS/ SPI1_MOSI	USB_DP
72	46	A8	A11	34	PA13	I/O	FT	JTMS-SWDIO	JTMS-SWDIO	-
73	-	-	C11	-	PH2	I/O	FT	PH2	-	-
74	47	D5	F11	35	V _{SS_2}	S	-	V _{SS_2}	-	-
75	48	E5	G11	36	V _{DD_2}	S	-	V _{DD_2}	-	-
76	49	A7	A10	37	PA14	I/O	FT	JTCK-SWCLK	JCTK-SWCLK	-
77	50	A6	A9	38	PA15	I/O	FT	JTDI	TIM2_CH1_ETR/PA15/ SPI1_NSS/ LCD_SEG17	-
78	51	B7	B11	-	PC10	I/O	FT	PC10	USART3_TX/ LCD_SEG28/ LCD_SEG40/ LCD_COM4	-
79	52	B6	C10	-	PC11	I/O	FT	PC11	USART3_RX/ LCD_SEG29/ LCD_SEG41/ LCD_COM5	-
80	53	C5	B10	-	PC12	I/O	FT	PC12	USART3_CK/ LCD_SEG30/ LCD_SEG42/ LCD_COM6	-
81	-	-	C9	-	PD0	I/O	FT	PD0	SPI2_NSS/TIM9_CH1	-

Table 9. STM32L151x6/8/B-A and STM32L152x6/8/B-A pin definitions (continued)

Pins					Pin name	Pin type ⁽¹⁾	I/O structure	Main function ⁽²⁾ (after reset)	Pins functions	
LQFP100	LQFP64	TFBGA64	UFBGA100	LQFP48 or UQFPN48					Alternate functions	Additional functions
98	-	-	A2	-	PE1	I/O	FT	PE1	LCD_SEG37/ TIM11_CH1	-
99	63	D4	D3	47	V _{SS_3}	S	-	V _{SS_3}	-	-
100	64	E4	C4	48	V _{DD_3}	S	-	V _{DD_3}	-	-

1. I = input, O = output, S = supply.

2. Function availability depends on the chosen device. For devices having reduced peripheral counts, it is always the lower number of peripheral that is included. For example, if a device has only one SPI and two USARTs, they will be called SPI1 and USART1 & USART2, respectively. Refer to [Table 2 on page 11](#).

3. Applicable to STM32L152xxxxA devices only. In STM32L151xxxxA devices, this pin should be connected to V_{DD}.

4. The PC14 and PC15 I/Os are only configured as OSC32_IN/OSC32_OUT when the LSE oscillator is on (by setting the LSEON bit in the RCC_CSR register). The LSE oscillator pins OSC32_IN/OSC32_OUT can be used as general-purpose PC14/PC15 I/Os, respectively, when the LSE oscillator is off (after reset, the LSE oscillator is off). The LSE has priority over the GPIO function. For more details, refer to Using the OSC32_IN/OSC32_OUT pins as GPIO PC14/PC15 port pins section in the STM32L1xxxx reference manual (RM0038).

5. The PH0 and PH1 I/Os are only configured as OSC_IN/OSC_OUT when the HSE oscillator is on (by setting the HSEON bit in the RCC_CR register). The HSE oscillator pins OSC_IN/OSC_OUT can be used as general-purpose PH0/PH1 I/Os, respectively, when the HSE oscillator is off (after reset, the HSE oscillator is off). The HSE has priority over the GPIO function.

6. Unlike in the LQFP64 package, there is no PC3 in the TFBGA64 package. The V_{REF+} functionality is provided instead.



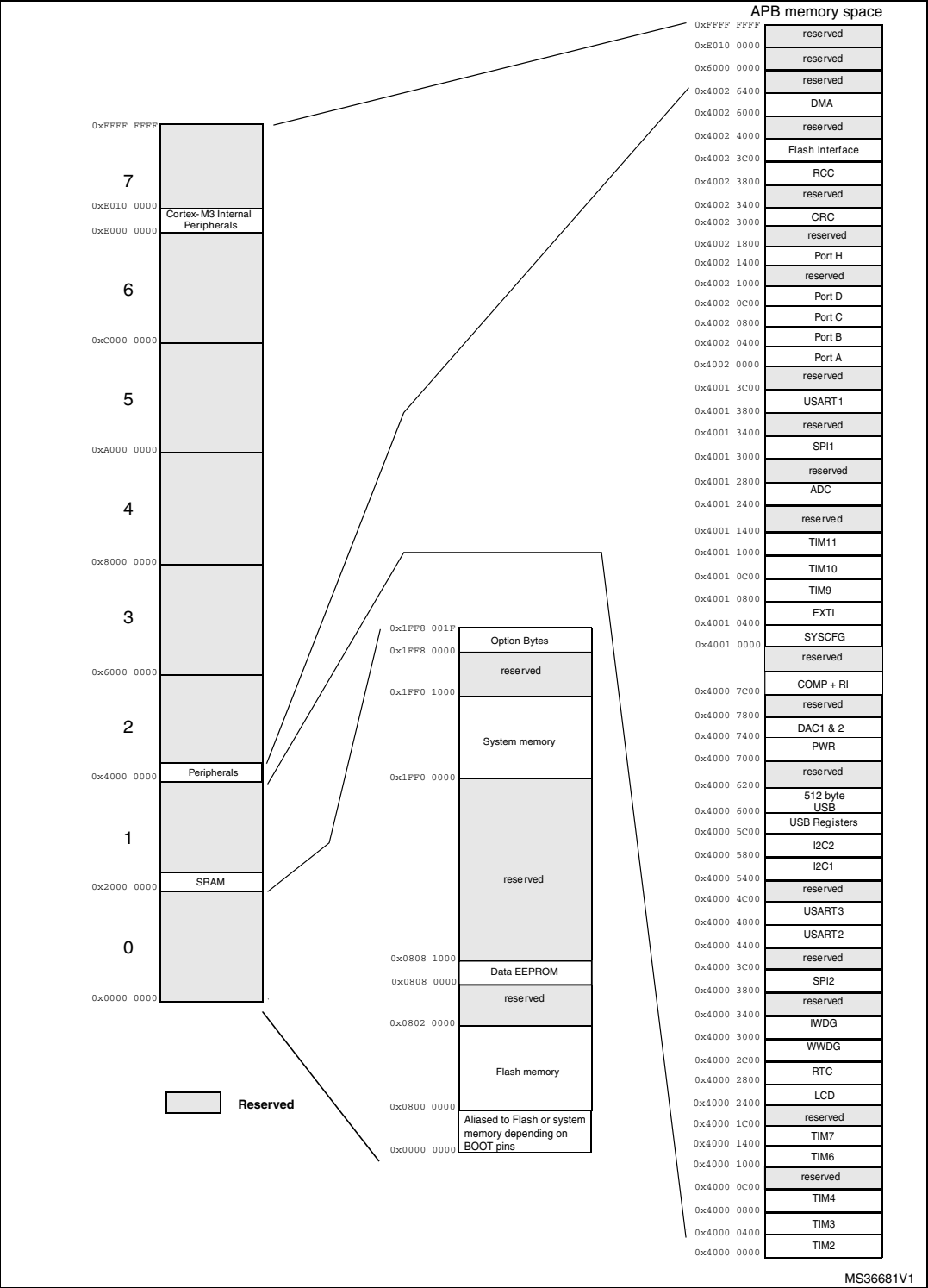
Table 10. Alternate function input/output (continued)

Port name	Digital alternate function number														
	AFIO0	AFIO1	AFIO2	AFIO3	AFIO4	AFIO5	AFIO6	AFIO7	AFIO8	AFIO9	AFIO11	AFIO12	AFIO13	AFIO14	AFIO15
	Alternate function														
	SYSTEM	TIM2	TIM3/4	TIM9/10/11	I2C1/2	SPI1/2	N/A	USART1/2/3	N/A	N/A	LCD	N/A	N/A	RI	SYSTEM
PC10	-	-	-	-	-	-	-	USART3_TX	-	-	COM4 / SEG28 / SEG40	-	-	TIMx_IC3	EVENTOUT
PC11	-	-	-	-	-	-	-	USART3_RX	-	-	COM5 / SEG29 / SEG41	-	-	TIMx_IC4	EVENTOUT
PC12	-	-	-	-	-	-	-	USART3_CK	-	-	COM6 / SEG30 / SEG42	-	-	TIMx_IC1	EVENTOUT
PC13-WKUP2	-	-	-	-	-	-	-	-	-	-	-	-	-	TIMx_IC2	EVENTOUT
PC14-OSC32_IN	-	-	-	-	-	-	-	-	-	-	-	-	-	TIMx_IC3	EVENTOUT
PC15-OSC32_OUT	-	-	-	-	-	-	-	-	-	-	-	-	-	TIMx_IC4	EVENTOUT
PD0	-	-	-	TIM9_CH1	-	SPI2_NSS	-	-	-	-	-	-	-	TIMx_IC1	EVENTOUT
PD1	-	-	-	-	-	SPI2_SCK	-	-	-	-	-	-	-	TIMx_IC2	EVENTOUT
PD2	-	-	TIM3_ETR	-	-	-	-	-	-	-	COM7 / SEG31 / SEG43	-	-	TIMx_IC3	EVENTOUT
PD3	-	-	-	-	-	SPI2_MISO	-	USART2_CTS	-	-	-	-	-	TIMx_IC4	EVENTOUT
PD4	-	-	-	-	-	SPI2_MOSI	-	USART2_RTS	-	-	-	-	-	TIMx_IC1	EVENTOUT
PD5	-	-	-	-	-	-	-	USART2_TX	-	-	-	-	-	TIMx_IC2	EVENTOUT
PD6	-	-	-	-	-	-	-	USART2_RX	-	-	-	-	-	TIMx_IC3	EVENTOUT
PD7	-	-	-	TIM9_CH2	-	-	-	USART2_CK	-	-	-	-	-	TIMx_IC4	EVENTOUT
PD8	-	-	-	-	-	-	-	USART3_TX	-	-	-	-	-	TIMx_IC1	EVENTOUT
PD9	-	-	-	-	-	-	-	USART3_RX	-	-	-	-	-	TIMx_IC2	EVENTOUT

5 Memory mapping

The memory map is shown in the following figure.

Figure 9. Memory map



MS36681V1

- Negative injection disturbs the analog performance of the device. See note in [Section 6.3.17](#).
- Positive current injection is not possible on these I/Os. A negative injection is induced by $V_{IN} < V_{SS}$. $I_{INJ(PIN)}$ must never be exceeded. Refer to [Table 11](#) for maximum allowed input voltage values.
- A positive injection is induced by $V_{IN} > V_{DD}$ while a negative injection is induced by $V_{IN} < V_{SS}$. $I_{INJ(PIN)}$ must never be exceeded. Refer to [Table 11: Voltage characteristics](#) for the maximum allowed input voltage values.
- When several inputs are submitted to a current injection, the maximum $\Sigma I_{INJ(PIN)}$ is the absolute sum of the positive and negative injected currents (instantaneous values).

Table 13. Thermal characteristics

Symbol	Ratings	Value	Unit
T_{STG}	Storage temperature range	-65 to +150	°C
T_J	Maximum junction temperature	150	°C
T_{LEAD}	Maximum lead temperature during soldering	see note ⁽¹⁾	°C

- Compliant with JEDEC Std J-STD-020D (for small body, Sn-Pb or Pb assembly), the ST ECOPACK® 7191395 specification, and the European directive on Restrictions on Hazardous Substances (ROHS directive 2011/65/EU, July 2011).

6.3 Operating conditions

6.3.1 General operating conditions

Table 14. General operating conditions

Symbol	Parameter	Conditions	Min	Max	Unit
f_{HCLK}	Internal AHB clock frequency	-	0	32	MHz
f_{PCLK1}	Internal APB1 clock frequency	-	0	32	
f_{PCLK2}	Internal APB2 clock frequency	-	0	32	
V_{DD}	Standard operating voltage	BOR detector disabled	1.65	3.6	V
		BOR detector enabled, at power on	1.8	3.6	
		BOR detector disabled, after power on	1.65	3.6	
$V_{DDA}^{(1)}$	Analog operating voltage (ADC and DAC not used)	Must be the same voltage as $V_{DD}^{(2)}$	1.65	3.6	V
	Analog operating voltage (ADC or DAC used)		1.8	3.6	
V_{IN}	I/O input voltage	FT pins: $2.0\text{ V} \leq V_{DD}$	-0.3	5.5 ⁽³⁾	V
		FT pins: $V_{DD} < 2.0\text{ V}$	-0.3	5.25 ⁽³⁾	
		BOOT0	0	5.5	
		Any other pin	-0.3	$V_{DD}+0.3$	

Table 14. General operating conditions (continued)

Symbol	Parameter	Conditions	Min	Max	Unit
P_D	Power dissipation at $T_A = 85\text{ °C}$ for suffix 6 or $T_A = 105\text{ °C}$ for suffix 7 ⁽⁴⁾	UFBGA100 package	-	339	mW
		LQFP100 package	-	435	
		TFBGA64 package	-	308	
		LQFP64 package	-	444	
		LQFP48 package	-	364	
		UFQFPN48 package	-	606	
T_A	Ambient temperature for 6 suffix version	Maximum power dissipation ⁽⁵⁾	-40	85	°C
	Ambient temperature for 7 suffix version	Maximum power dissipation	-40	105	
T_J	Junction temperature range	6 suffix version	-40	105	°C
	Junction temperature range	7 suffix version	-40	110	

1. When the ADC is used, refer to [Table 55: ADC characteristics](#).
2. It is recommended to power V_{DD} and V_{DDA} from the same source. A maximum difference of 300 mV between V_{DD} and V_{DDA} can be tolerated during power-up and operation.
3. To sustain a voltage higher than $V_{DD}+0.3\text{ V}$, the internal pull-up/pull-down resistors must be disabled.
4. If T_A is lower, higher P_D values are allowed as long as T_J does not exceed $T_{J\text{ max}}$ (see [Table 13: Thermal characteristics on page 56](#)).
5. In low-power dissipation state, T_A can be extended to -40 °C to 105 °C temperature range as long as T_J does not exceed $T_{J\text{ max}}$ (see [Table 13: Thermal characteristics on page 56](#)).

6.3.2 Embedded reset and power control block characteristics

The parameters given in the following table are derived from the tests performed under the ambient temperature condition summarized in the following table.

Table 15. Embedded reset and power control block characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$t_{VDD}^{(1)}$	V_{DD} rise time rate	BOR detector enabled	0	-	∞	$\mu\text{s/V}$
		BOR detector disabled	0	-	1000	
	V_{DD} fall time rate	BOR detector enabled	20	-	∞	
		BOR detector disabled	0	-	1000	
$T_{RSTTEMPO}^{(1)}$	Reset temporization	V_{DD} rising, BOR enabled	-	2	3.3	ms
		V_{DD} rising, BOR disabled ⁽²⁾	0.4	0.7	1.6	
$V_{POR/PDR}$	Power on/power down reset threshold	Falling edge	1	1.5	1.65	V
		Rising edge	1.3	1.5	1.65	

Table 18. Current consumption in Run mode, code with data processing running from Flash

Symbol	Parameter	Conditions		f _{HCLK}	Typ	Max ⁽¹⁾	Unit
I _{DD} (Run from Flash)	Supply current in Run mode, code executed from Flash	f _{HSE} = f _{HCLK} up to 16 MHz, included f _{HSE} = f _{HCLK} /2 above 16 MHz (PLL ON) ⁽²⁾	Range 3, V _{CORE} =1.2 V VOS[1:0] = 11	1 MHz	215	285	μA
				2 MHz	400	490	
				4 MHz	725	1000	
			Range 2, V _{CORE} =1.5 V VOS[1:0] = 10	4 MHz	0.915	1.3	mA
				8 MHz	1.75	2.15	
				16 MHz	3.4	4	
			Range 1, V _{CORE} =1.8 V VOS[1:0] = 01	8 MHz	2.1	2.9	
				16 MHz	4.2	5.2	
				32 MHz	8.25	9.6	
		HSI clock source (16 MHz)	Range 2, V _{CORE} =1.5 V VOS[1:0] = 10	16 MHz	3.5	4.4	
			Range 1, V _{CORE} =1.8 V VOS[1:0] = 01	32 MHz	8.2	10.2	
		MSI clock, 65 kHz	Range 3, V _{CORE} =1.2 V VOS[1:0] = 11	65 kHz	0.041	0.085	
		MSI clock, 524 kHz		524 kHz	0.125	0.180	
		MSI clock, 4.2 MHz		4.2 MHz	0.775	0.935	

1. Guaranteed by characterization results, unless otherwise specified.

2. Oscillator bypassed (HSEBYP = 1 in RCC_CR register).

Table 20. Current consumption in Sleep mode

Symbol	Parameter	Conditions		f _{HCLK}	Typ	Max ⁽¹⁾	Unit
I _{DD} (Sleep)	Supply current in Sleep mode, Flash OFF	f _{HSE} = f _{HCLK} up to 16 MHz included, f _{HSE} = f _{HCLK} /2 above 16 MHz (PLL ON) ⁽²⁾	Range 3, V _{CORE} =1.2 V VOS[1:0] = 11	1 MHz	50	155	μA
				2 MHz	78.5	235	
				4 MHz	140	370 ⁽³⁾	
			Range 2, V _{CORE} =1.5 V VOS[1:0] = 10	4 MHz	165	375	
				8 MHz	310	530	
				16 MHz	590	1000	
			Range 1, V _{CORE} =1.8 V VOS[1:0] = 01	8 MHz	350	615	
				16 MHz	680	1200	
				32 MHz	1600	2350	
		HSI clock source (16 MHz)	Range 2, V _{CORE} =1.5 V VOS[1:0] = 10	16 MHz	640	970	
			Range 1, V _{CORE} =1.8 V VOS[1:0] = 01	32 MHz	1600	2350	
		MSI clock, 65 kHz	Range 3, V _{CORE} =1.2 V VOS[1:0] = 11	65 kHz	19	60	
		MSI clock, 524 kHz		524 kHz	33	90	
		MSI clock, 4.2 MHz		4.2 MHz	145	210	
	Supply current in Sleep mode, Flash ON	f _{HSE} = f _{HCLK} up to 16 MHz included, f _{HSE} = f _{HCLK} /2 above 16 MHz (PLL ON) ⁽²⁾	Range 3, V _{CORE} =1.2 V VOS[1:0] = 11	1 MHz	60.5	145	μA
				2 MHz	89.5	225	
				4 MHz	150	360	
			Range 2, V _{CORE} =1.5 V VOS[1:0] = 10	4 MHz	180	370	
				8 MHz	320	490	
				16 MHz	605	895	
			Range 1, V _{CORE} =1.8 V VOS[1:0] = 01	8 MHz	380	565	
				16 MHz	695	1070	
				32 MHz	1600	2200	
		HSI clock source (16 MHz)	Range 2, V _{CORE} =1.5 V VOS[1:0] = 10	16 MHz	650	970	
			Range 1, V _{CORE} =1.8 V VOS[1:0] = 01	32 MHz	1600	2320	
		MSI clock, 65 kHz	Range 3, V _{CORE} =1.2V VOS[1:0] = 11	65 kHz	29.5	65	
		MSI clock, 524 kHz		524 kHz	44	80	
		MSI clock, 4.2 MHz		4.2 MHz	155	220	

1. Guaranteed by characterization results, unless otherwise specified.
2. Oscillator bypassed (HSEBYP = 1 in RCC_CR register)
3. Guaranteed by test in production.

Table 52. USB DC electrical characteristics

Symbol	Parameter	Conditions	Min. ⁽¹⁾	Max. ⁽¹⁾	Unit
Input levels					
V _{DD}	USB operating voltage ⁽²⁾	-	3.0	3.6	V
V _{DI} ⁽³⁾	Differential input sensitivity	I(USB_DP, USB_DM)	0.2	-	V
V _{CM} ⁽³⁾	Differential common mode range	Includes V _{DI} range	0.8	2.5	
V _{SE} ⁽³⁾	Single ended receiver threshold	-	1.3	2.0	
Output levels					
V _{OL} ⁽⁴⁾	Static output level low	R _L of 1.5 kΩ to 3.6 V ⁽⁵⁾	-	0.3	V
V _{OH} ⁽⁴⁾	Static output level high	R _L of 15 kΩ to V _{SS} ⁽⁵⁾	2.8	3.6	

1. All the voltages are measured from the local ground potential.
2. To be compliant with the USB 2.0 full speed electrical specification, the USB_DP (D+) pin should be pulled up with a 1.5 k Ω resistor to a 3.0-to-3.6 V voltage range.
3. Guaranteed by characterization results.
4. Guaranteed by test in production.
5. R_L is the load connected on the USB drivers.

Figure 25. USB timings: definition of data signal rise and fall time

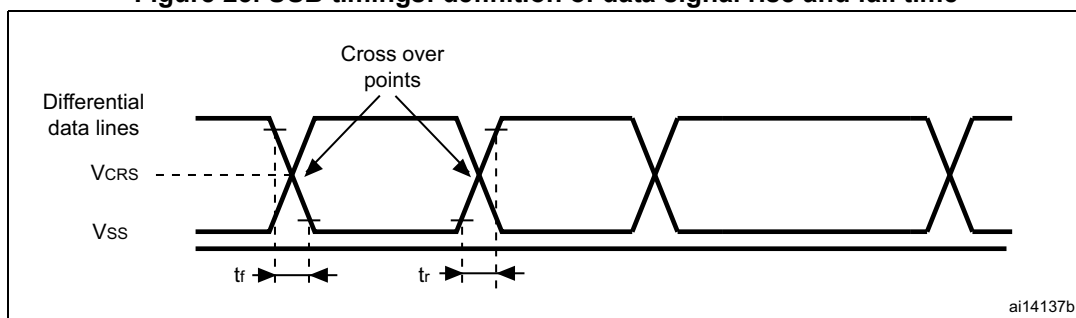


Table 53. USB: full speed electrical characteristics

Driver characteristics ⁽¹⁾					
Symbol	Parameter	Conditions	Min	Max	Unit
t_r	Rise time ⁽²⁾	$C_L = 50$ pF	4	20	ns
t_f	Fall Time ⁽²⁾	$C_L = 50$ pF	4	20	ns
t_{rfm}	Rise/ fall time matching	t_r/t_f	90	110	%
V_{CRS}	Output signal crossover voltage	-	1.3	2.0	V

1. Guaranteed by design.
2. Measured from 10% to 90% of the data signal. For more detailed informations, please refer to USB Specification section 7 (version 2.0).

6.3.18 DAC electrical specifications

Data guaranteed by design, unless otherwise specified.

Table 58. DAC characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{DDA}	Analog supply voltage	-	1.8	-	3.6	V
V_{REF+}	Reference supply voltage	V_{REF+} must always be below V_{DDA}	1.8	-	3.6	V
V_{REF-}	Lower reference voltage	-	V_{SSA}			V
$I_{DDVREF+}^{(1)}$	Current consumption on V_{REF+} supply $V_{REF+} = 3.3$ V	No load, middle code (0x800)	-	130	220	μ A
		No load, worst code (0x000)	-	220	350	μ A
$I_{DDA}^{(1)}$	Current consumption on V_{DDA} supply $V_{DDA} = 3.3$ V	No load, middle code (0x800)	-	210	320	μ A
		No load, worst code (0xF1C)	-	320	520	μ A
R_L	Resistive load	DAC output buffer ON Connected to V_{SSA}	5	-	-	k Ω
		Connected to V_{DDA}	25	-	-	
C_L	Capacitive load	DAC output buffer ON	-	-	50	pF
R_O	Output impedance	DAC output buffer OFF	12	16	20	k Ω
V_{DAC_OUT}	Voltage on DAC_OUT output	DAC output buffer ON	0.2	-	$V_{DDA} - 0.2$	V
		DAC output buffer OFF	0.5	-	$V_{REF+} - 1\text{LSB}$	mV
DNL ⁽¹⁾	Differential non linearity ⁽²⁾	$C_L \leq 50$ pF, $R_L \geq 5$ k Ω DAC output buffer ON	-	1.5	3	LSB
		No R_L , $C_L \leq 50$ pF DAC output buffer OFF	-	1.5	3	
INL ⁽¹⁾	Integral non linearity ⁽³⁾	$C_L \leq 50$ pF, $R_L \geq 5$ k Ω DAC output buffer ON	-	2	4	
		No R_L , $C_L \leq 50$ pF DAC output buffer OFF	-	2	4	
Offset ⁽¹⁾	Offset error at code 0x800 ⁽⁴⁾	$C_L \leq 50$ pF, $R_L \geq 5$ k Ω DAC output buffer ON	-	± 10	± 25	
		No R_L , $C_L \leq 50$ pF DAC output buffer OFF	-	± 5	± 8	
Offset1 ⁽¹⁾	Offset error at code 0x001 ⁽⁵⁾	No R_L , $C_L \leq 50$ pF DAC output buffer OFF	-	± 1.5	± 5	

7.5 UFBGA100 7 x 7 mm, 0.5 mm pitch, ultra thin fine-pitch ball grid array package information

Figure 42. UFBGA100, 7 x 7 mm, 0.5 mm pitch, ultra thin fine-pitch ball grid array package outline

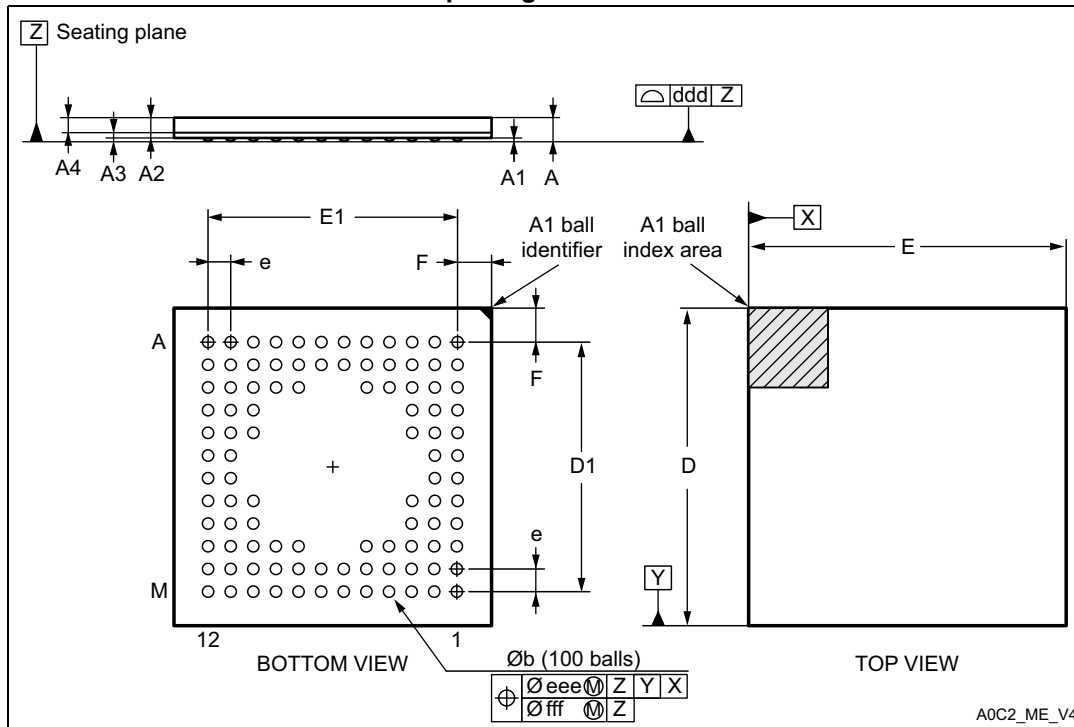
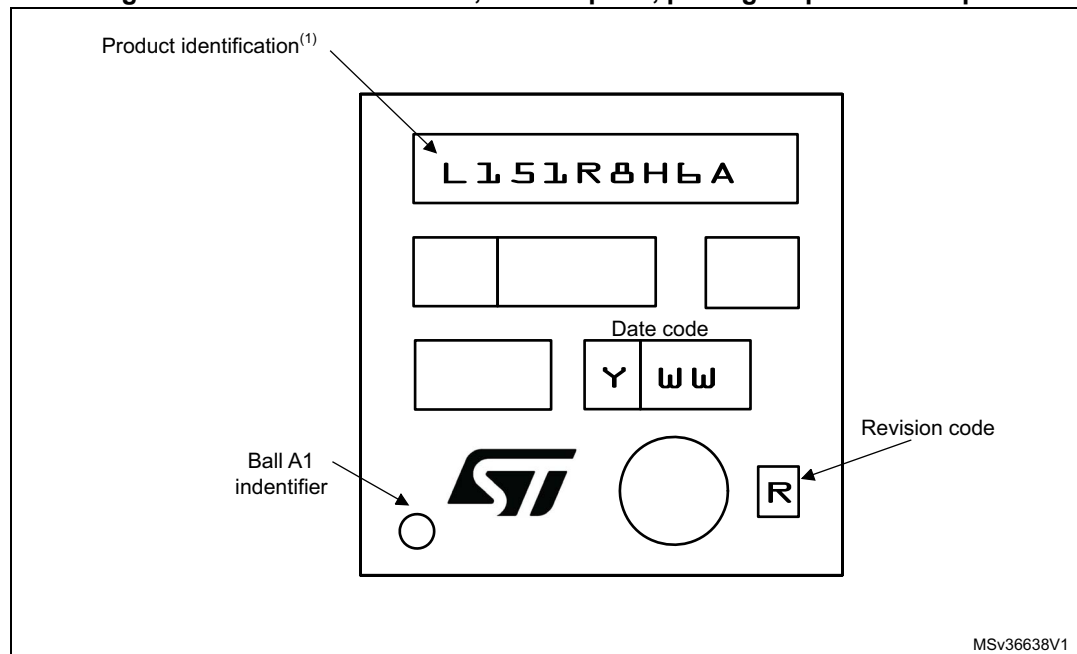


Table 68. UFBGA100 7 x 7 mm, 0.5 mm pitch, ultra thin fine-pitch ball grid array package mechanical data

Symbol	millimeters			inches ⁽¹⁾		
	Min	Typ	Max	Min	Typ	Max
A	-	-	0.6	-	-	0.0236
A1	0.05	0.08	0.11	0.002	0.0031	0.0043
A2	0.4	0.45	0.5	0.0157	0.0177	0.0197
A3	0.08	0.13	0.18	0.0031	0.0051	0.0071
A4	0.27	0.32	0.37	0.0106	0.0126	0.0146
b	0.2	0.25	0.3	0.0079	0.0098	0.0118
D	6.95	7	7.05	0.2736	0.2756	0.2776
D1	5.45	5.5	5.55	0.2146	0.2165	0.2185
E	6.95	7	7.05	0.2736	0.2756	0.2776
E1	5.45	5.5	5.55	0.2146	0.2165	0.2185
e	-	0.5	-	-	0.0197	-

TFBGA64 device marking

The following figure gives an example of topside marking orientation versus ball A1 identifier location.

Figure 47. TFBGA64 5 x 5 mm, 0.5 mm pitch, package top view example

1. Parts marked as "ES", "E" or accompanied by an Engineering Sample notification letter, are not yet qualified and therefore not yet ready to be used in production and any consequences deriving from such usage will not be at ST charge. In no event, ST will be liable for any customer usage of these engineering samples in production. ST Quality has to be contacted prior to any decision to use these Engineering samples to run qualification activity.

8 Ordering information

Table 73. Ordering information scheme

Example:	STM32	L	152	R	B	T	6	A	D	TR
Device family										
STM32 = ARM-based 32-bit microcontroller										
Product type										
L = Low-power										
Device subfamily										
151: Devices without LCD										
152: Devices with LCD										
Pin count										
C = 48 pins										
R = 64 pins										
V = 100 pins										
Flash memory size										
6 = 32 Kbytes of Flash memory										
8 = 64 Kbytes of Flash memory										
B = 128 Kbytes of Flash memory										
Package										
H = BGA										
T = LQFP										
U = UFQFPN										
Temperature range										
6 = Industrial temperature range, -40 to 85 °C										
7 = Industrial temperature range, -40 to 105 °C										
Options										
A = device generation A										
No character = VDD range: 1.8 to 3.6 V and BOR enabled										
D = VDD range: 1.65 to 3.6 V and BOR disabled										
Packing										
TR = tape and reel										
No character = tray or tube										

For a list of available options (speed, package, etc.) or for further information on any aspect of this device, please contact your nearest ST sales office.

IMPORTANT NOTICE – PLEASE READ CAREFULLY

STMicroelectronics NV and its subsidiaries ("ST") reserve the right to make changes, corrections, enhancements, modifications, and improvements to ST products and/or to this document at any time without notice. Purchasers should obtain the latest relevant information on ST products before placing orders. ST products are sold pursuant to ST's terms and conditions of sale in place at the time of order acknowledgement.

Purchasers are solely responsible for the choice, selection, and use of ST products and ST assumes no liability for application assistance or the design of Purchasers' products.

No license, express or implied, to any intellectual property right is granted by ST herein.

Resale of ST products with provisions different from the information set forth herein shall void any warranty granted by ST for such product.

ST and the ST logo are trademarks of ST. All other product or service names are the property of their respective owners.

Information in this document supersedes and replaces information previously supplied in any prior versions of this document.

© 2016 STMicroelectronics – All rights reserved

